TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC4S69F

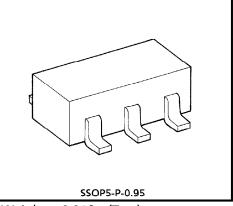
INVERTER GATE

The TC4S69F is three stage inverter.

The output is provided with the buffer, the input/output voltage characteristic has been improved. Thus an increase in propagation delay time caused by an increase in load capacity is kept to a minimum.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
DC Supply Voltage	V_{DD}	$V_{SS} - 0.5 \sim V_{SS} + 20$	V
Input Voltage	V _{IN}	$V_{SS} - 0.5 \sim V_{DD} + 0.5$	V
Output Voltage	VOUT	$V_{SS} - 0.5 \sim V_{DD} + 0.5$	٧
DC Input Current	IN	± 10	mA
Power Dissipation	PD	200	mW
Operating Temperature Range	T _{opr}	- 40∼85	°C
Storage Temperature Range	T _{stg}	- 65~150	°C
Lead Temperature (10s)	TL	260	°C

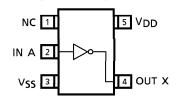


Weight: 0.016g (Typ.)

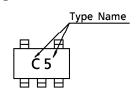
LOGIC DIAGRAM

IN A O OUT X

PIN CONFIGURATION (TOP VIEW)



MARKING



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RECOMMENDED OPERATING CONDITIONS $(V_{SS} = 0V)$

CHARACTERISTIC	SYMBOL		MIN.	TYP.	MAX.	UNIT
DC Supply Voltage	V_{DD}	_	3	_	18	V
Input Voltage	V _{IN}		0	_	V_{DD}	V

STATIC ELECTRICAL CHARACTERISTICS $(V_{SS} = 0V)$

CHARACTERISTIC SY		TEST CONDITION	V_{DD}	– 40°C		25°C			85°C		UNIT
BOL	BOL	TEST CONDITION	(V)	MIN.	MAX.	MIN.	TYP.	MAX.	MIN.	MAX.	ONIT
High-Level			5	4.95	_	4.95	5.00	_	4.95	_	
Output Voltage	I _{OUT} >1μΑ V _{IN} =V _{SS}	10	9.95		9.95	10.00	—	9.95			
	VIIV - 422	15	14.95		14.95			14.95		V	
Low-Level	 I _{OUT} <1μΑ	5	_	0.05	_	0.00	l	—	0.05	Ů	
Output Voltage	VOL	$V_{IN} = V_{DD}$	10	_	0.05		0.00	l	<u> </u>	0.05	
- Catput Voltage			15	_	0.05	_	0.00			0.05	
		V _{OH} = 4.6V	5	- 0.61		- 0.51	- 1.0	l	- 0.42		
Output High		$V_{OH} = 2.5V$	5	- 2.5		- 2.1	- 4.0	l	- 1.7		
Current	IOH	V _{OH} = 9.5V	10	- 1.5		- 1.3	- 2.2	ı	- 1.1		
Carrent		V _{OH} = 13.5V	15	- 4.0	_	- 3.4	- 9.0	—	- 2.8	_	
		V _{IN} = V _{SS}									mA
		$V_{OL} = 0.4V$	5	0.61		0.51	1.2	l	0.42		A
Output Low	lOL	V _{OL} = 0.5V	10	1.5		1.3	3.2	t	1.1	t	
Current	'OL	V _{OL} = 1.5V	15	4.0	_	3.4	12.0	—	2.8	_	
		$V_{IN} = V_{DD}$									
		V _{OUT} = 0.5V	5	3.5	-	3.5	2.75	_	3.5		
Input High Voltage	\ \ \ \	V _{OUT} = 1.0V	10	7.0	_	7.0	5.5	_	7.0	_	
Imput high voltage	VIH	V _{OUT} = 1.5V	15	11.0	_	11.0	8.25	—	11.0	_	
		l _{OUT} <1μΑ									v
Input Low Voltage V		V _{OUT} = 4.5V	5	_	1.5	_	2.25	1.5	_	1.5	·
	.,	V _{OUT} = 9.0V	10	_	3.0		4.5	3.0	_	3.0	
	V_{IL}	V _{OUT} = 13.5V	15	_	4.0	<u> </u>	6.75	4.0	l —	4.0	
		l _{OUT} <1μΑ									
Input H Level	ΊΗ	V _{IH} = 18V	18	_	0.1	_	10 ⁻⁵	ı	_	1.0	
Current L Level	կլ	V _{IL} = 0V	18	_	- 0.1	_	- 10 ^{- 5}	- 0.1	_	- 1.0	μ A
Quiescent Device Current			5	_	0.25	_	0.001	0.25	_	7.5	
	IDD	$V_{IN} = V_{SS}, V_{DD}$	10	_	0.5	-	0.001	0.5	—	15	μ A
Device Current			15	_	1.0	_	0.002	1.0	_	30	

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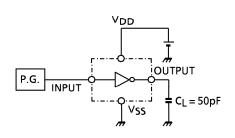
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DYNAMIC ELECTRICAL CHARACTERISTICS (Ta = 25°C, V_{SS} = 0V, C_L = 50pF)

CHARACTERISTIC	SYMBOL	TEST CONDITION VDD (V		MIN.	TYP.	MAX.	UNIT
Output Transition Time			5	_	70	200	
(Low to High)	tTLH	_	10	_	35	100	
(Low to High)			15	_	30	80	
Output Transition Time			5	_	70	200	ns
Output Transition Time (High to Low)	^t THL	_	10	_	35	100	
			15	_	30	80	
	t _{pLH}		5	_	65	200	
Propagation Delay Time		_	10	_	30	100	
			15	_	25	80	
	t _{pHL}		5	_	65	200	ns
Propagation Delay Time		_	10	_	30	100	
			15	_	25	80	
Input Capacitance	C _{IN}	_	_	5	7.5	pF	

CIRCUIT AND WAVEFORM FOR MEASUREMENT OF DYNAMIC CHARACTERISTICS

TEST CIRCUIT



WAVEFORM

